To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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HAT2038R/HAT2038RJ

Silicon N Channel Power MOS FET
High Speed Power Switching

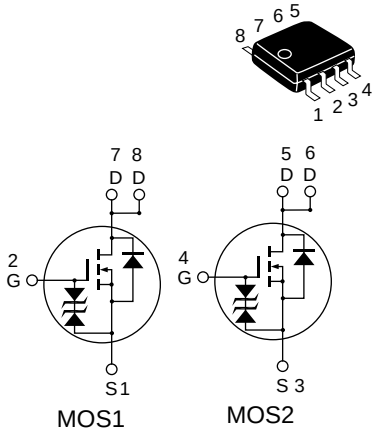
ADE-208-666C (Z)
4th. Edition
Feb. 1999

Features

- For Automotive Application (at Type Code “J “)
- Low on-resistance
- Capable of 4 V gate drive
- High density mounting

Outline

SOP–8



1, 3	Source
2, 4	Gate
5, 6, 7, 8	Drain

Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage		V_{DSS}	60	V
Gate to source voltage		V_{GSS}	± 20	V
Drain current		I_D	5	A
Drain peak current		$I_{D(pulse)}$ Note1	40	A
Body-drain diode reverse drain current		I_{DR}	5	A
Avalanche current	HAT2038R	I_{AP} Note4	—	—
	HAT2038RJ		5	A
Avalanche energy	HAT2038R	E_{AR} Note4	—	—
	HAT2038RJ		2.14	mJ
Channel dissipation		Pch Note2	2	W
Channel dissipation		Pch Note3	3	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	– 55 to + 150	°C

Note: 1. PW ≤ 10μs, duty cycle ≤ 1 %
2. 1 Drive operation : When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW≤ 10s
3. 2 Drive operation : When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW≤ 10s
4. Value at Tch=25°C, Rg≥50Ω

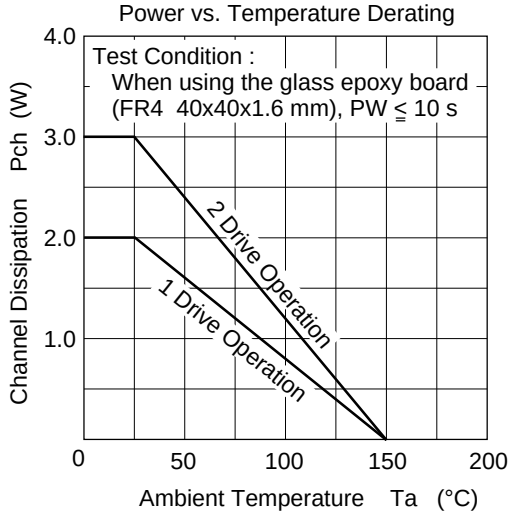
Electrical Characteristics (Ta = 25°C)

Item		Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage		$V_{(BR)DSS}$	60	—	—	V	I_D = 10 mA, V_{GS} = 0
Gate to source breakdown voltage		$V_{(BR)GSS}$	± 20	—	—	V	I_G = ± 100 µA, V_{DS} = 0
Gate to source leak current		I_{GSS}	—	—	± 10	µA	V_{GS} = ± 16 V, V_{DS} = 0
Zero gate voltage	HAT2038R	I_{DSS}	—	—	1	µA	V_{DS} = 60 V, V_{GS} = 0
drain current	HAT2038RJ	I_{DSS}	—	—	0.1	µA	
Zero gate voltage	HAT2038R	I_{DSS}	—	—	—	µA	V_{DS} = 48 V, V_{GS} = 0
drain current	HAT2038RJ	I_{DSS}	—	—	10	µA	Ta = 125°C
Gate to source cutoff voltage		$V_{GS(off)}$	1.2	—	2.2	V	V_{DS} = 10 V, I_D = 1 mA
Static drain to source on state resistance		$R_{DS(on)}$	—	0.043	0.058	Ω	I_D = 3 A, V_{GS} = 10 V Note5
		$R_{DS(on)}$	—	0.056	0.084	Ω	I_D = 3 A, V_{GS} = 4 V Note5
Forward transfer admittance		$\|y_{fs}\|$	6	9	—	S	I_D = 3 A, V_{DS} = 10 V Note5
Input capacitance		Ciss	—	520	—	pF	V_{DS} = 10 V
Output capacitance		Coss	—	270	—	pF	V_{GS} = 0
Reverse transfer capacitance		Crss	—	100	—	pF	f = 1MHz
Turn-on delay time		$t_{d(on)}$	—	11	—	ns	V_{GS} =10 V, I_D = 3 A
Rise time		t_r	—	40	—	ns	V_{DD} ≅ 30 V
Turn-off delay time		$t_{d(off)}$	—	110	—	ns	
Fall time		t_f	—	80	—	ns	
Body–drain diode forward voltage		V_{DF}	—	0.84	1.1	V	IF = 5 A, V_{GS} = 0 Note5
Body–drain diode reverse recovery time		t_{rr}	—	40	—	ns	IF = 5 A, V_{GS} = 0 diF/ dt = 50 A/µs

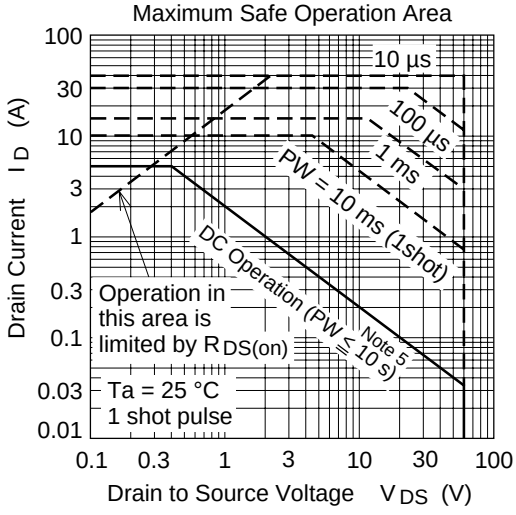
Note: 5. Pulse test

Main Characteristics

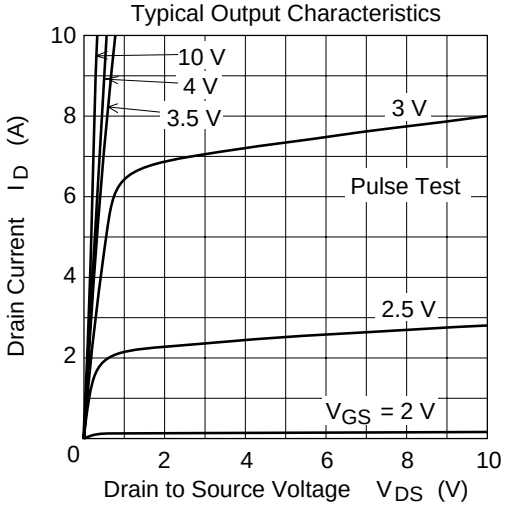
Power vs. Temperature Derating



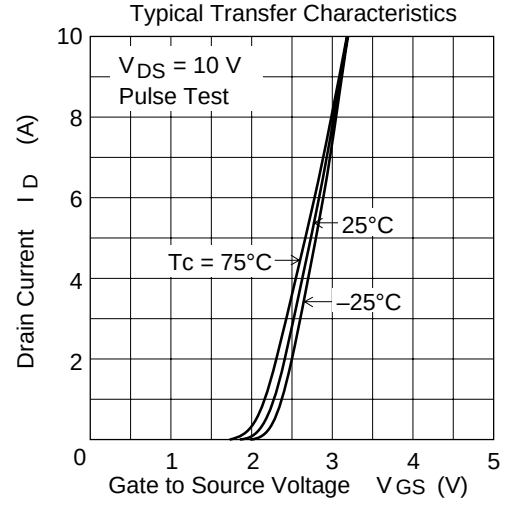
Maximum Safe Operation Area



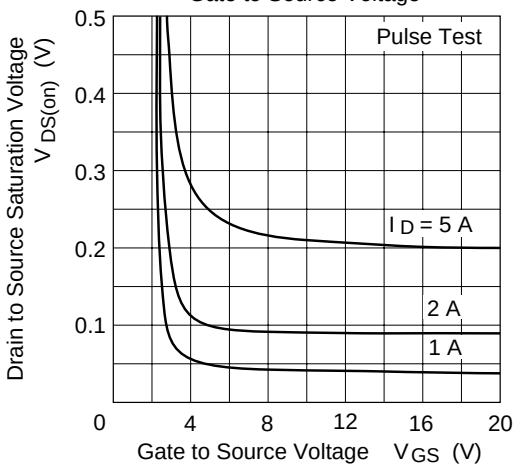
Typical Output Characteristics



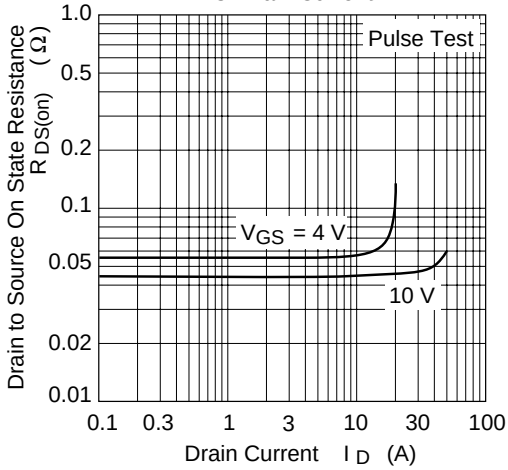
Typical Transfer Characteristics



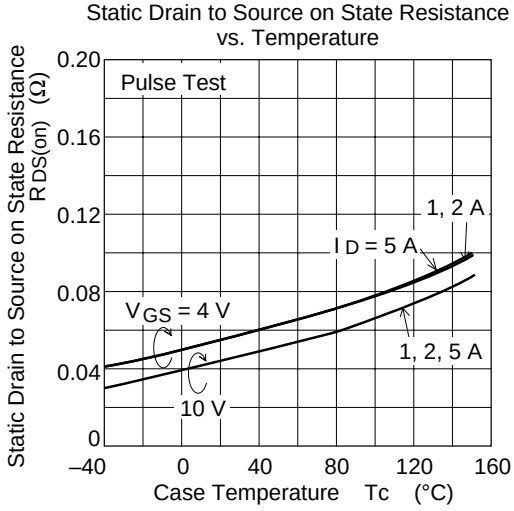
Drain to Source Saturation Voltage vs. Gate to Source Voltage



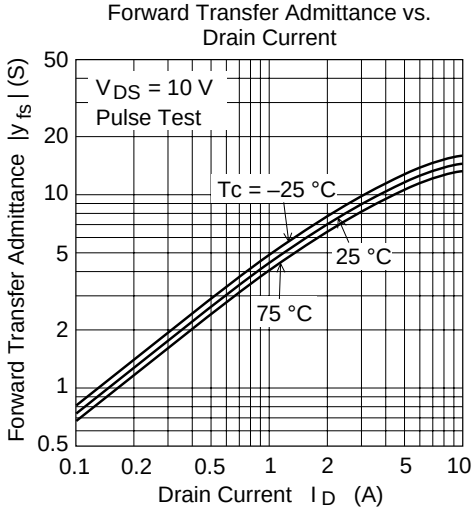
Static Drain to Source on State Resistance vs. Drain Current



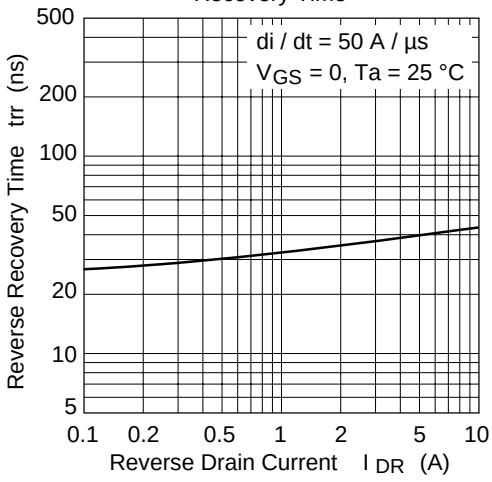
Static Drain to Source on State Resistance vs. Temperature



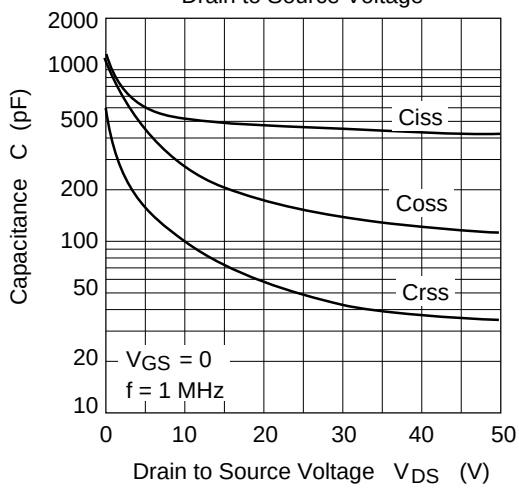
Forward Transfer Admittance vs. Drain Current



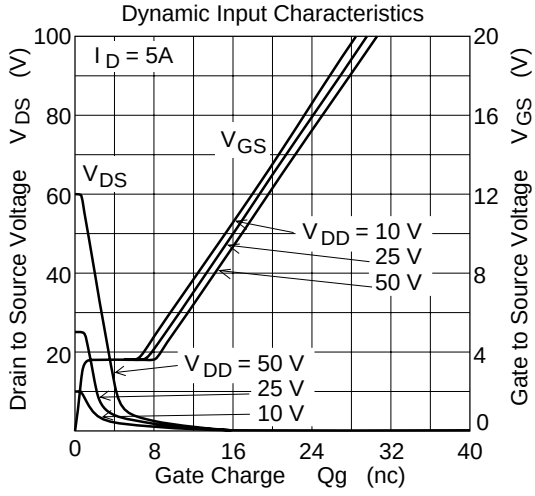
Body–Drain Diode Reverse Recovery Time



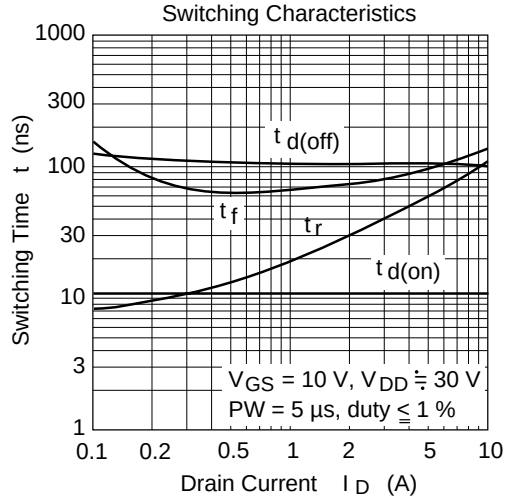
Typical Capacitance vs. Drain to Source Voltage



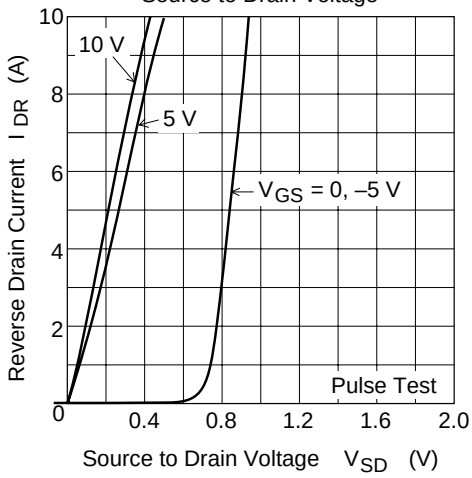
Dynamic Input Characteristics



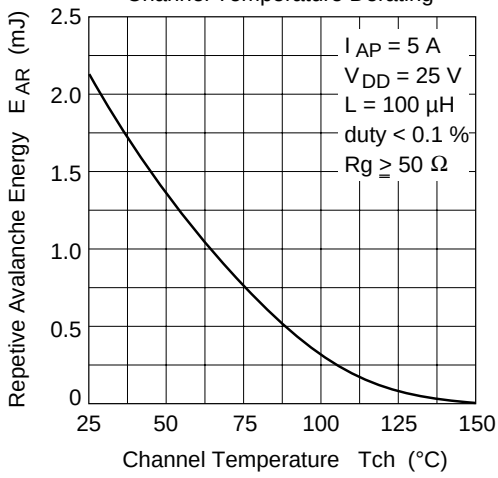
Switching Characteristics



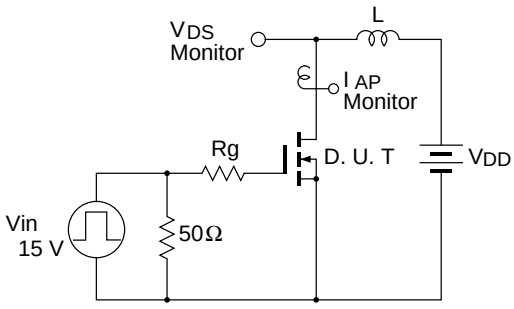
Reverse Drain Current vs.
Source to Drain Voltage



Maximun Avalanche Energy vs.
Channel Temperature Derating

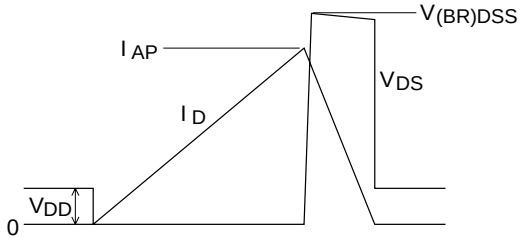


Avalanche Test Circuit

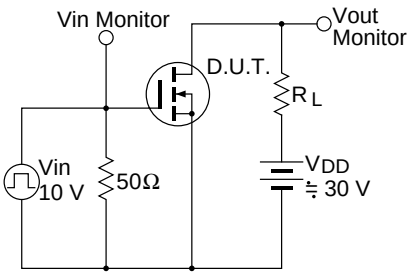


Avalanche Waveform

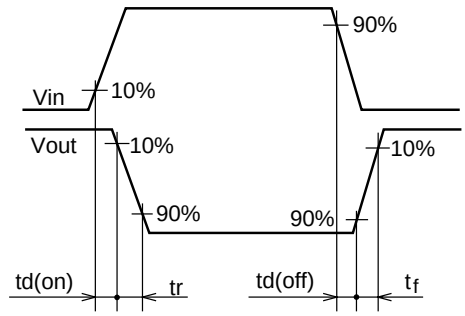
$$E_{AR} = \frac{1}{2} \bullet L \bullet {I_{AP}}^2 \bullet \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



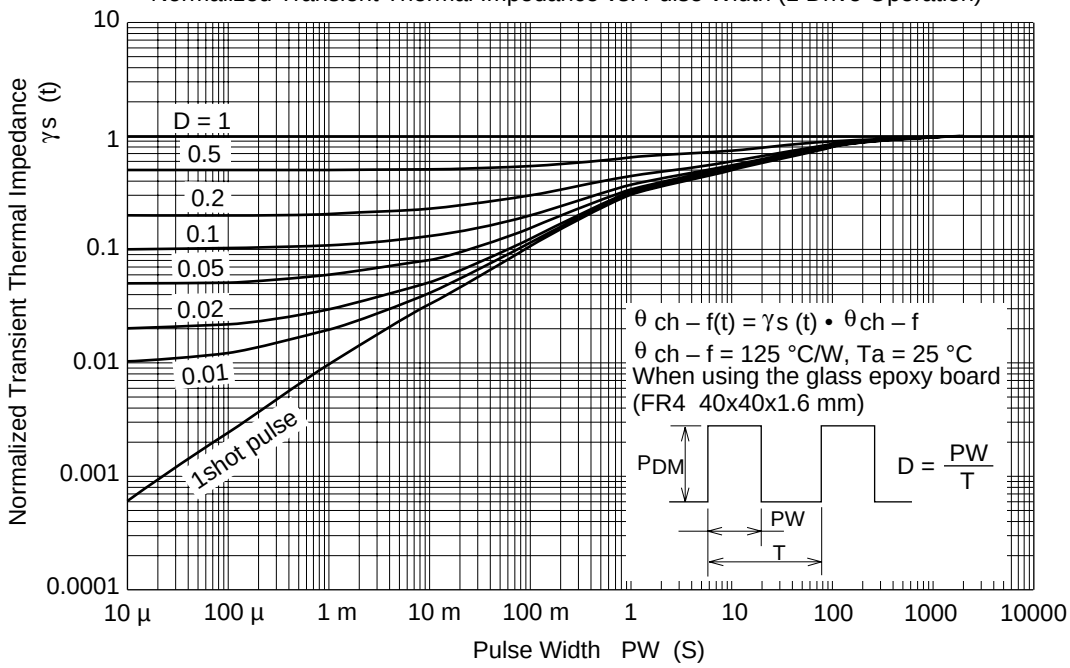
Switching Time Test Circuit



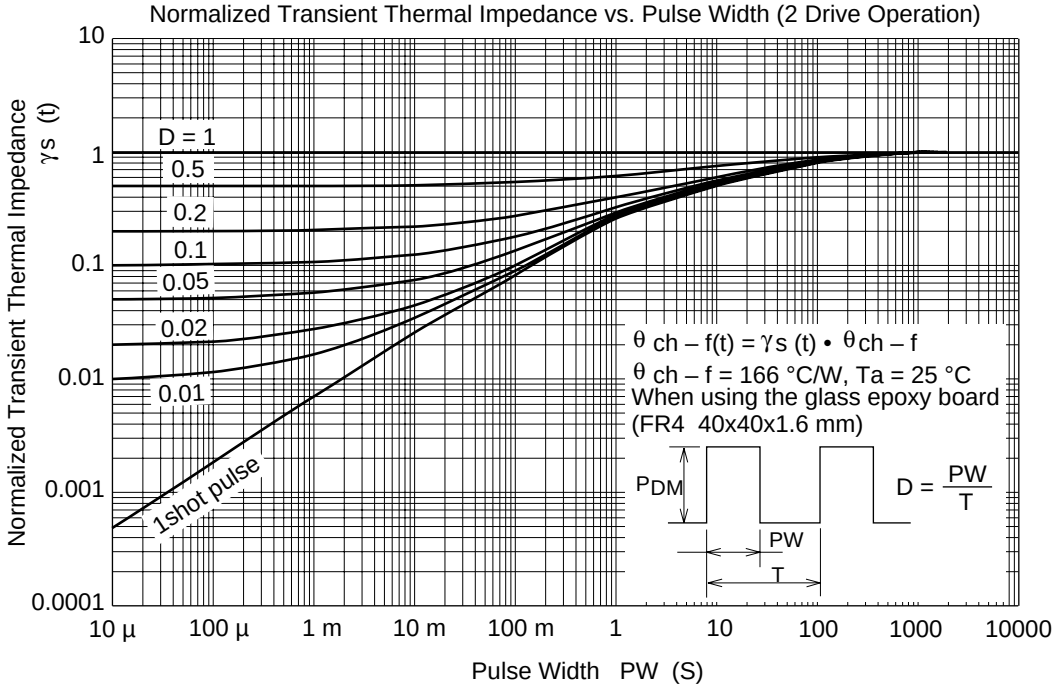
Switching Time Waveform



Normalized Transient Thermal Impedance vs. Pulse Width (1 Drive Operation)



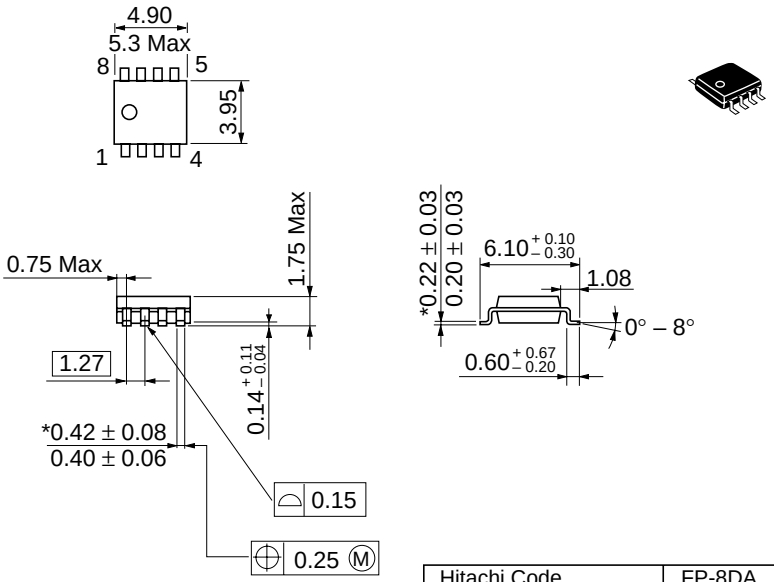
Normalized Transient Thermal Impedance vs. Pulse Width (2 Drive Operation)



Package Dimensions

As of January, 2001

Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-8DA
JEDEC	Conforms
EIAJ	—
Mass (reference value)	0.085 g

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HITACHI

Hitachi, Ltd.
Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : http://semiconductor.hitachi.com/
Europe : http://www.hitachi-eu.com/hel/ecg
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For further information write to:

Hitachi Semiconductor (America) Inc.
179 East Tasman Drive,
San Jose,CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straβe 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel : <65>-538-6533/538-8577
Fax : <65>-538-6933/538-3877
URL : http://www.hitachi.com.sg

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel : <886>-(2)-2718-3666
Fax : <886>-(2)-2718-8180
Telex : 23222 HAS-TP
URL : http://www.hitachi.com.tw

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
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